

SN65LVDS314

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PROGRAMMABLE 27-BIT SERIAL-TO-PARALLEL RECEIVER

Check for Samples: SN65LVDS314

FEATURES

- Serial Interface Technology
- Compatible with FlatLink[™]3G such as SN65LVDS301 and SN65LVDS311
- Supports Video Interfaces up to 24-bit RGB Data and 3 Control Bits Received over 1, 2 or 3 SubLVDS Differential Lines
- SubLVDS Differential Voltage Levels
- Flexible RGB Signaling Level of 1.8 V to 3.3 V
- Up to 1.755 Gbps Data Throughput
- Three Operating Modes to Conserve Power
 - Active mode QVGA 17 mW
 - Typical Shutdown 0.6 μW
 - Typical Standby Mode 54 μW Typical
- Bus-Swap Function for PCB-Layout Flexibility
- ESD Rating > 4 kV (HBM)
- Pixel Clock Range of 4 MHz-65 MHz
- Failsafe on all CMOS Inputs
- Packaged in 8 mm x 8 mm QFN with 0.4 mm pin pitch
- Very low EMI meets SAE J1752/3 'Kh'-spec

APPLICATIONS

- Small Low-Emission Interface between Graphics Controller and LCD Display
- Cameras, Camcorders, Embedded Computers
- Portable Multimedia Players

DESCRIPTION

The SN65LVDS314 receiver de-serializes FlatLink[™]3G compliant serial input data to 27 parallel data outputs. The SN65LVDS314 receiver contains one shift register to load 30 bits from 1, 2 or 3 serial inputs and latches the 24 pixel bits and 3 control bits out to the parallel CMOS outputs after checking the parity bit. If the parity check confirms correct parity, the Channel Parity Error (CPE) output remains low. If a parity error is detected, the CPE output generates a high pulse while the data output bus disregards the newly-received pixel. Instead, the last data word is held on the output bus for another clock cycle. The serial data and clock are received via Sub Low-Voltage Differential Signalling (SubLVDS) lines. The SN65LVDS314 supports three operating power modes (Shutdown, Standby, and Active) to conserve power.

When receiving, the PLL locks to the incoming clock CLK and generates an internal high-speed clock at the line rate of the data lines. The data is serially loaded into a shift register using the internal high-speed clock. The deserialized data is presented on the parallel output bus with a recreation of the Pixel clock PCLK generated from the internal high-speed clock. If no input CLK signal is present, the output bus is held static with the PCLK and DE held low, while all other parallel outputs are pulled high.

The parallel (CMOS) output bus offers a bus-swap feature. The SWAP control pin controls the output pin order of the output pixel data to be either R[7:0]. G[7:0], B[7:0], VS, HS, DE or B[0:7], G[0:7], R[0:7], VS, HS, DE. This gives a PCB designer the flexibility to better match the bus to the LCD driver pinout or to put the receiver device on the top side or the bottom side of the PCB. The F/S control input selects between a slow CMOS bus output rise time for best EMI and power consumption and a fast CMOS output for increased speed or higher load designs.



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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

DESCRIPTION (CONTINUED)

Two Link Select lines LS0 and LS1 select whether 1, 2, or 3 serial links are used. The RXEN input may be used to put the SN65LVDS314 in a Shutdown mode. The SN65LVDS314 enters an active Standby mode if the common mode voltage of the CLK input becomes shifted to VDDLVDS (e.g., transmitter releases the CLK output into high-impedance). This minimizes power consumption without the need of switching an external control pin. The SN65LVDS314 is characterized for operation over ambient air temperatures of -40° C to 85°C. All CMOS and SubLVDS signals are 2-V tolerant with V_{DD} = 0 V. This feature allows signal powerup before V_{DD} is stabilized.



FUNCTIONAL BLOCK DIAGRAM



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PINOUT - TOP VIEW RSK PACKAGE (TOP VIEW) B1/R6 CPOL **B7/R0 B4/R**3 **B2/R5 B5/R2** B3/R4 PCLK B0/R7 **B6/R1** GND GND F/S 48 40 39 38 35 47 46 45 44 43 42 41 37 36 34 G0/G7 49 50 51 52 53



RGB output pin assignment based on SWAP pin setting: SWAP = 0 / SWAP = 1

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SWAP PIN FUNCTIONALITY

The SWAP pin allows the pcb designer to reverse the RGB bus, minimizing potential signal crossovers due to signal routing. The two drawings beneath show the RGB signal pin assignment based on the SWAP-pin setting.



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Figure 2. Pinout With SWAP PIN = VDD

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		Table 1. Pin Description							
PIN	SWAP	SIGNAL	PIN	SWAP .	SIGNAL	PIN	SWAP	SIGNAL	
4	L	R5	22			40	L	B5	
I	Н	B2	22	-	GND_LVDS	43	Н	R2	
2	L	R6	22			4.4	L	B6	
Z	Н	B1	23	-	VDD_LVDS	44	Н	R1	
2	L	R7	04			45	L	B7	
3	Н	B0	24	-	VDD_LVDS	45	Н	R0	
4	-	LS0	25	-	SWAP	46	-	GND	
5	-	VDD	26	-	GND_PLLA	47	-	VDD_IO	
6	-	LS1	27	-	VDD_PLLA	48	-	CPOL	
_							L	G0	
7	-	VDD_PLLD	28	-	RXEN	49	Н	G7	
							L	G1	
8	-	GND_PLLD	29	-	VS	50	н	G6	
							L	G2	
9	-	VDD_LVDS	30	-	CPE	51	Н	G5	
							L	G3	
10	-	GND_LVDS	31	-	VDD	52	Н	G4	
							L	G4	
11	-	D2+	32	-	HS	53	Н	G3	
							L	G5	
12	-	D2-	33	-	DE	54	Н	G2	
							L	G6	
13	-	GND_LVDS	34	-	VDD_IO	55	Н	G1	
							L	G7	
14	-	D1+	35	-	F/S	56	Н	G0	
15	-	D1-	36	_	PCLK	57	_	GND	
16	-	GND LVDS	37	_	GND	58	-	VDD IO	
-			-	L	B0				
17	-	CLK+	38	Н	R7	59	-	VDD	
				L	B1		L	R0	
18	-	CLK-	39	Н	R6	60	Н	B7	
				L	B2		L	R1	
19	-	GND_LVDS	40	H	R5	61	Н	B6	
		+ +		L	B3		L	R2	
20	-	D0+	41	- H	 R4	62		B5	
		+ + +		L	B4		L	R3	
21	-	D0-	42	-	 R3	63		B4	
					1.0			R4	
						64	<u></u> н	R3	



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TERMINAL FUNCTIONS

NAME	I/O	DESCRIPTION
D0+, D0–		SubLVDS Data Link (active during normal operation)
D1+, D1–	- SubLVDS in	SubLVDS Data Link (active during normal operation when LS0 = high and LS1 = low, or LS0 = low and LS1=high; high impedance if LS0 = LS1 = low); input can be left open if unused
D2+, D2–		SubLVDS Data Link (active during normal operation when LS0 = low and LS1 = high, high-impedance when LS1 = low); input can be left open if unused
CLK+, CLK-		SubLVDS Input Pixel Clock; Polarity is fixed.
R0–R7		Red Pixel Data (8); pin assignment depends on SWAP pin setting
G0–G7	CMOS out	Green Pixel Data (8); pin assignment depends on SWAP pin setting
B0–B7		Blue Pixel Data (8); pin assignment depends on SWAP pin setting
HS		Horizontal Sync
VS		Vertical Sync
DE		Data Enable
PCLK		Output Pixel Clock; rising or falling clock polarity is selected by control input CPOL
LS0, LS1		Link Select (Determines active SubLVDS Data Links and PLL Range) See Table 2
		Disables the CMOS Drivers and Turns Off the PLL, putting device in shutdown mode
		1 – Reciver enabled 0 – Receiver disabled (Shutdown)
RXEN		Note: RXEN input incorporates glitch suppression logic to avoid unwanted switching. The input must be pulled low for longer than 10µs continuously to force the receiver to enter Shutdown. The input must be pulled high for at least 10µs continuously to activate the receiver. An input pulse shorter than 5us will be interpreted as glitch and becomes ignored. At power up, the receiver is enabled immediately if RXEN=H and disabled if RXEN=L
	CMOS in	Output Clock Polarity Selection
CPOL		0 – rising edge clocking 1 – falling edge clocking
C)A(A D		Bus Swap swaps the bus pins to allow device placement on top or bottom of PCB. See pinout drawing for pin assignments.
SWAP		0 – data output from R7B0 1 – data output from B0R7
		CMOS bus rise time select
F/S		1 – fast output rise time 0 – slow output rise time
CPE	CMOS out	Channel Parity Error This output indicates the detection of a parity error by generating an output high-pulse for half of a PCLK clock cycle; this allows counting parity errors with a simple counter.
		high-pulse – bit error detected
V _{DD}		Supply Voltage
V _{DD IO}		RGB interface supply voltage
GND		Supply Ground
V _{DDLVDS}		SubLVDS I/O supply Voltage
GND _{LVDS}	Power Supply	SubLVDS Ground
V _{DDPLLA}		PLL analog supply Voltage
GND _{PLLA}		PLL analog GND
V _{DDPLLD}		PLL digital supply Voltage
GND _{PLLD}		PLL digital GND

FUNCTIONAL DESCRIPTION

Deserialization Modes

The SN65LVDS314 receiver has three modes of operation controlled by link-select pins LS0 and LS1. Table 2 shows the deserializer modes of operation.

LS1	LS0		Mode of Operation	Data Links Status
0	0	1ChM	1-channel mode (30-bit serialization rate)	D0 active; D1, D2 disabled
0	1	2ChM	2-channel mode (15-bit serialization rate)	D0, D1 active; D2 disabled
1	0	3ChM	3-channel mode (10-bit serialization rate)	D0, D1, D2 active
1	1		Reserved	Reserved

Table 2. Logic Table: Link Select Operating Modes

1-Channel Mode

While LS0 and LS1 are held low, the SN65LVDS314 receives payload data over a single SubLVDS data pair, D0. The PLL locks to the SubLVDS clock input and internally multiplies the clock by a factor of 30. The internal high speed clock is used to shift in the data payload on D0 and to deserialize 30 bits of data. Figure 3 illustrates the timing and the mapping of the data payload into the 30-bit frame. The internal high speed clock is divided by a factor of 30 to recreate the pixel clock and the data payload with the pixel clock is presented on the output bus. The reserved bits and parity bit are not output. While in this mode, the PLL can lock to a clock that is in the range of 4 MHz through 15 MHz. This mode is intended for smaller video display formats that do not need the full bandwidth capabilities of the SN65LVDS314.



Figure 3. Data and Clock Input in 1-ChM (LS0 and LS1 = low)

2-Channel Mode

While LS0 is held high and LS1 is held low, the SN65LVDS314 receives payload data over two SubLVDS data pairs, D0 and D1. The PLL locks to the SubLVDS clock input and internally multiplies the clock by a factor of 15. The internal high speed clock is used to shift in the data payload on D0 and D1 and to deserialize 15 bits of data from each pair. Figure 4 illustrates the timing and the mapping of the data payload into the 30-bit frame. The internal high speed clock is divided by a factor of 15 to recreate the pixel clock, and the data payload with pixel clock is presented on the output bus. The reserved bits and parity bit are not output. While in this mode the PLL can lock to a clock that is in the range of 8 MHz through 30 MHz.





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3-Channel Mode

While LS0 is held low and LS1 is held high the SN65LVDS314 receives payload data over three SubLVDS data pairs: D0, D1, and D2. The PLL locks to the SubLVDS clock input and internally multiplies the clock by a factor of 10. The internal high speed clock is used to shift in the data payload on D0, D1, and D2, and to deserialize 10 bits of data from each pair. Figure 5 illustrates the timing and the mapping of the data payload into the 30-bit frame. While in this mode the PLL can lock to a clock that is in the range of 20 MHz through 65 MHz.



Figure 5. Data and Clock Input in 3-ChM (LS0 = low; LS1 = high)

POWERDOWN MODES

The SN65LVDS314 Receiver has two powerdown modes to facilitate efficient power management.

SHUTDOWN MODE

A low input signal on the RXEN pin puts the SN65LVDS314 into Shutdown mode. This turns off most of the receiver circuitry including the SubLVDS receivers, PLL, and deserializers. The subLVDS differential-input resistance remains 100 Ω , while any input signal is ignored. All outputs will hold a static output pattern:

R[0:7]=G[0:7]=B[0:7]=VS=HS=high; DE=PCLK=low.

The current draw in Shutdown mode will be nearly zero if the subLVDS inputs are left open or pulled high.

STANDBY MODE

The SN65LVDS314 will enter the Standby mode when the SN65LVDS314 is not in Shutdown mode but the SubLVDS clock-input common-mode voltage is above $0.9 \times V_{DDLVDS}$. The CLK input incorporates a pull-up circuit to shift the SubLVDS clock-input common-mode voltage to V_{DDLVDS} in the absence of an input signal. All circuitry except the SubLVDS clock-input Standby monitor is shut down. The SN65LVDS314 will also enter Standby mode when the input clock frequency on the CLK input is less than 500 kHz. The SubLVDS input resistance remains 100 Ω while any input signal on the data inputs D0, D1, and D2 becomes ignored. All outputs will hold a static output pattern:

R[0:7]=G[0:7]=B[0:7]=VS=HS=high; DE=PCLK=low.

The current drawn in Standby mode will be very low.

ACTIVE MODES

A high input signal on RXEN combined with a CLK input signal switching faster than 3 MHz and V_{ICM} smaller than 1.3 V force the SN65LVDS314 into Active mode. Current consumption in active mode depends on operating frequency and the number of data transitions in the data payload. CLK-input frequencies between 3 MHz and 4 MHz activate the device but proper PLL functionality is not secured. It is not recommended to operate the SN65LVDS314 in active mode at CLK frequencies below 4 MHz.

ACQUIRE MODE (PLL Approaches Lock)

When the SN65LVDS314 is enabled and a SubLVDS clock input present, the PLL will pursue lock to the input clock. While the PLL pursues lock the output data bus will hold a static output pattern:

R[0:7]=G[0:7]=B[0:7]=VS=HS=high; DE=PCLK=low.

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For proper device operation, the pixel clock frequency must fall within the valid f_{PCLK} range specified under recommended operating conditions. If the pixel clock frequency is larger than 3 MHz but smaller than $f_{PCLK(min)}$, the SN65LVDS314 PLL is enabled. Under such conditions, it is possible for the PLL to lock temporarily to the pixel clock, causing the PLL monitor to release the device into active receive mode. If this happens, the PLL may or may not be properly locked to the pixel clock input, potentially causing data errors, frequency oscillation, and PLL deadlock (loss of VCO oscillation).

RECEIVE MODE

After the PLL achieves lock the device enters the normal receive mode. The output data bus presents the deserialized data. The PCLK output pin outputs the recovered pixel clock.

PARITY ERROR DETECTION AND HANDLING

The SN65LVDS314 receiver performs error checking on the basis of a parity bit that is transmitted across the subLVDS interface from the transmitting device. Once the SN65LVDS314 detects the presence of the clock and the PLL has locked onto PCLK, then the parity is checked. Parity-error detection ensures detection of all single bit errors in one pixel and 50% of all multi-bit errors.

The parity bit covers the 27 bit data payload consisting of 24 bits of pixel data plus VS, HS, and DE. Odd Parity bit signalling is used. The parity error is output on the CPE pin. If the sum of the 27 data bits and the parity bit result in an odd number, the receive data are assumed to be valid. The CPE output will be held low. If the sum equals an even number, parity error is declared. The CPE output will indicate high for half a PCLK period. The CPE output will be set with the data bit transition and cleared after 1/2 the data bit time. This allows counting every detected parity error with a simple counter connected to CPE.



Also if there is a parity error detected then the data on that PCLK cycle is not output. Instead, the last valid data from a previous PCLK cycle is repeated on the output bus. This is to prevent any bit error that may occur on the LVDS link from causing perturbations in VS, HS, or DE that may be visually disruptive to a display.

The reserved bits are not covered in the parity calculations.



STATUS DETECT AND OPERATING MODES FLOW DIAGRAM

The SN65LVDS314 switches between the power saving and active modes in the following way:



Table 3. Status Detect and Operating Modes Descriptions

Mode	Characteristics	Conditions
Shutdown Mode	Least amount of power consumption (most circuitry turned off); All outputs held static: R[0:7]=G[0:7]=B[0:7]=VS=HS=high DE=PCLK=low;	RXEN is set low for longer than 10 μ s ⁽¹⁾ ⁽²⁾
Standby Mode	Low power consumption (Standby monitor circuit active; PLL is shutdown to conserve power); All outputs held static: R[0:7]=G[0:7]=B[0:7]=VS=HS=high DE=PCLK=low;	RXEN is high for longer than 10 $\mu s,$ and both CLK input common-mode $V_{ICM(CLK)}$ above $0.9 \times V_{DDLVDS},$ or CLK input floating $^{(2)}$
Acquire Mode	PLL pursues lock; All outputs held static: R[0:7]=G[0:7]=B[0:7]=VS=HS=high DE=PCLK=low;	RXEN is high; CLK input monitor detected clock input common mode and woke up receiver out of Standby mode
Receive Mode	Data transfer (normal operation); receiver deserializes data and provides data on parallel output	RXEN is high and PLL is locked to incoming clock

(1) In Shutdown Mode, all SN65LVDS314 internal switching circuits (e.g., PLL, serializer, etc.) are turned off to minimize power consumption. The input stage of any input pin remains active.

(2) Leaving CMOS control inputs unconnected can cause random noise to toggle the input stage and potentially harm the device. All CMOS inputs must be tied to a valid logic level V_{IL} or V_{IH} during Shutdown or Standby Mode. Exceptions are the subLVDS inputs CLK and Dx, which can be left unconnected while not in use.

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MODE TRANSITION	USE CASE	TRANSITION SPECIFICS
Shutdown \rightarrow Standby	Drive RXEN high to enable	1. RXEN high > 10 μs
	receiver	2. Receiver enters standby mode
		a. R[0:7]=G[0:7]=B[0:7]=VS=HS remain high and DE=PCLK low
		b. Receiver activates clock input monitor
Standby \rightarrow Acquire	Transmitter activity	1. CLK input monitor detects clock input activity
	detected	2. Outputs remain static
		3. PLL circuit is enabled
Acquire \rightarrow Receive	Link is ready to receive	1. PLL is active and approaches lock
	data	2. PLL achieves lock within twakeup
		3. D1, D2, and/or D3 become active depending on LS0 and LS1 selection
		4. First Data word was recovered
		Parallel output bus turns on switching from static output pattern to output first valid data word
Receive \rightarrow Standby	Transmitter requested to	1. Receiver disables outputs within t _{standby}
	enter Standby mode by	2. RX Input monitor detects $V_{ICM} > 0.9 \text{ VDD}_{LVDS}$ within $t_{standby}$
	voltage $V_{ICM} > 0.9 V_{DDLVDS}$ (e.g. transmitter output	 R[0:7]=G[0:7]=B[0:7]=VS=HS transition to high and DE=PCLK to low on next falling PLL clock edge
	clock stops or enters high- impedance state)	4. PLL shuts down. Clock activity input monitor remains active
Receive/Standby \rightarrow	Turn off Receiver	 RXEN pulled low for > t_{pwrdn}
Shutdown		 R[0:7]=G[0:7]=B[0:7]=VS=HS remain static high or transition to static high and DE=PCLK remain or transition to static low
		3. Most IC circuitry is shut down for least power consumption

Table 4. Operating Mode Transitions

RGB Signaling Level

The signaling level of the R[0:7], G[0:7], B[0:7], HS, VS, DE, and PCLK outputs of the SN65LVDS314 can be configured to be between 1.8 V and 3.3 V (nominal), depending on the voltage applied to the VDD_IO terminals. This provides compatibility with LCD drivers with interface voltages between 1.8 V and 3.3 V without the need for external level shifters.

Product Folder Links : SN65LVDS314

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ABSOLUTE MAXIMUM RATINGS⁽¹⁾

		VALUE	UNIT	
Supply voltage range, V _{DD} ⁽²⁾ , V _{DDPLLA} , V _{DDPLLD} , V _{DDLVDS}		-0.3 to 2.175	V	
Supply voltage range, V _{DD}	10	–0.3 to 3.6	V	
Voltage range at any input	When VDDx > 0 V	-0.5 to 2.175		
or output terminal When $VDDx \le 0 V$ Human Body Model ⁽³⁾ (all Pins) Electrostatic discharge Charged-Device Mode ⁽⁴⁾ (all Pins)	–0.5 to V _{DD} + 2.175	v		
	Human Body Model ⁽³⁾ (all Pins)	±4	kV	
Electrostatic discharge	Charged-Device Mode ⁽⁴⁾ (all Pins)	±1000	V	
	Machine Model ⁽⁵⁾ (all pins)	±200	v	
Continuous power dissipation	n	See Dissipation Rating	g Table	
Ouput current, I _O		±5	mA	
Storage temperature, T _{STG}		-65 to 150	°C	
Maximum junction temperature, TJ		125	°C	

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute maximum-rated conditions for extended periods may affect device reliability.

All voltage values are with respect to the GND terminals

(3)

In accordance with JEDEC Standard 22, Test Method A114-B In accordance with JEDEC Standard 22, Test Method C101 (4)

In accordance with JEDEC Standard 22, Test Method A115-A (5)

THERMAL INFORMATION

		SN65LVDS314	
		RSK	UNITS
		64 PINS	
θ_{JA}	Junction-to-ambient thermal resistance ⁽²⁾	31.7	
θ _{JCtop}	Junction-to-case (top) thermal resistance ⁽³⁾	20	
θ_{JB}	Junction-to-board thermal resistance ⁽⁴⁾	9.9	80 M
Ψ _{JT}	Junction-to-top characterization parameter ⁽⁵⁾	0.3	°C/W
Ψ _{JB}	Junction-to-board characterization parameter ⁽⁶⁾	9.9	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance ⁽⁷⁾	2.4	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as (2) specified in JESD51-7, in an environment described in JESD51-2a.

The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDECstandard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

(4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.

The junction-to-top characterization parameter, ψ_{JT} , estimates the junction temperature of a device in a real system and is extracted (5) from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).

The junction-to-board characterization parameter, ψ_{JB} , estimates the junction temperature of a device in a real system and is extracted (6)from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).

The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific (7) JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

DEVICE POWER DISSIPATION

PARAMETER		TEST CONDITIONS			MAX	UNIT
P _D		1/2 1.9. $1/2$ 25% of autouto terminated with 10 pF	f _{CLK} at 4 MHz	12.8		~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~
	Device Power	$v_{DDx} = 1.8 \text{ v}, T_A = 25 \text{ C}, an outputs terminated with To pr$	f _{CLK} at 65 MHz	59.2		mvv
	Dissipation	$V_{DD} = V_{DDPLLA} = V_{DDPLLD} = V_{DDLVDS} = 1.95 \text{ V}, V_{DD} \text{ IO} = 3.6 \text{ V},$	f _{CLK} at 4 MHz		41	m\//
		all outputs terminated with 10 pF	f _{CLK} at 65 MHz		261.9	IIIVV

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STRUMENTS

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RECOMMENDED OPERATING CONDITIONS⁽¹⁾

Vop VopELA VopELDA VopELOB Supply voltages 1.65 1.8 1.95 V Vop. Io Supply voltage for CMOS outputs 1.65 1.8 1.95 V Vop. Io Supply voltage noise magnitude 50MHz (all supplies) Test set-up see Figure 7 [CLK \$ 50MHz; (inoise) = 1Hz to 2 GHz 100 mV T_C Case temperature 100 100 7 0 85 °C C Case temperature -40 85 °C °C °C CLK+ and CLK- -40 85 °C °C °C °C CLK+ and CLK -40 85 °C °C °C °C CLK+ and CLK- -40 85 °C °C °C °C CLK+ and CLK- -40 85 °C °C °C °C Magnitude of differential input Voltage Cock frequency 1-Channel receive mode, see Figure 3 4 15 °C Vicin Magnitude of differential input voltage Vicin<-Vicin+ Vicin+				MIN	TYP MAX	UNIT		
$\begin{tabular}{ c c c c c } \hline Supply voltage for CMOS outputs & 1.85 & 3.6 & V \\ \hline V_{DDn(PP)} & Supply voltage noise magnitude \\ \hline SUPPLY voltage noise magnitude \\ \hline SUPLY voltage noise noise noise magnit$	V _{DD} V _{DDPLLA} V _{DDPLLD} V _{DDLVDS}	Supply voltages		1.65	1.8 1.95	V		
$\begin{split} & \text{VDDn(PP)} \\ & \text{Supply voltage noise magnitude} \\ & \text{SOMHz (all supplies)} \\ & \text{Test set-up see Figure 7} \\ & \text{f}_{CLK} \leq \text{SOMHz (trainspace from the see Figure 1} \\ & \text{Test set-up see Figure 2} \\ & \text{Test set-up see Figure 1} \\ & \text{Test set-up see Figure 2} \\ & \text{Test set-up see Figure 3} \\ & \text{Test set-up see Figure 3} \\ & \text{Test set-up see Figure 3} \\ & \text{Test set-up see Figure 4} \\ & \text{Test set-up see Figure 4} \\ & \text{Test set-up see Figure 5} \\ & \text{Test set-up see Figure 6} \\ & \text{Test set-up see Figure 10} \\ & \text{Test set set volt see figure 10} \\ & Test set set set set set set set set set $	V _{DD_IO}	Supply voltage for CMOS outputs		1.65	3.6	V		
$\begin{split} & \begin{array}{c} \mbox{V}_{\text{DDn(PP)}} & \begin{array}{c} \mbox{Supply voltage noise magnitude} \\ \mbox{SOMH2 (all supplies)} & \begin{array}{c} \mbox{f}_{\text{CLK}} \leq 50MH2; \mbox{f(noise)} = 1H2 to 2 \ GHZ & 100 \\ \hline \mbox{f}_{\text{CLK}} > 50MH2; \mbox{f(noise)} = 1H2 to 1MH2 & 100 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} = 1H2 to 1MH2 & 100 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MH2 & 40 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MP2 & 80 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MP2 & 80 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 1MP2 & 50 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 50 \ MH2 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 50 \ MH2 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 50 \ MH2 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2; \mbox{f(noise)} > 50 \ MH2 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2 \ MH2 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2 \ MH2 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2 \ MH2 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2 \ MH2 \ MH2 \\ \hline \mbox{f}_{\text{CLK}} > 50 \ MH2 \ M$			Test set-up see Figure 7					
VDDn(PP) 50MHz (all supplies) t_{CLK} > 50MHz; f(noise) = 1Hz to 1MHz 100 Inv T_A Operating free-air temperature -40 85 °C T_C Case temperature 93.1 °C CLK+ and CLK- -40 85 °C fcLK and CLK- 93.1 °C fcLK and CLK- -20 65 2-Channel receive mode, see Figure 3 4 15 3-Channel receive mode, see Figure 4 8 30 3-Channel receive mode, see Figure 5 20 66 Standby mode ⁽²⁾ , See Figure 16 500 kHz vbuTCLK CLK Input Duty Cycle 35 65 % D0+, D0-, D1+, D1-, D2+, D2-, CLK+, and CLK- Vicuk-VcLK-l during normal operation 70 200 mV VicM Input Voltage Common Mode Range Receive or Acquire mode 0.6 1.2 V AV _{ICM} Input Voltage Common Mode Vicuk-VCLK-l during normal operation mV mV VicM Input Voltage Amplitude Vicuk and m=D0, D1, D2, or CLK -100 100	V	Supply voltage noise magnitude	$f_{CLK} \le 50MHz$; f(noise) = 1Hz to 2 GHz		100	m\/		
$ \begin{array}{ c c c c c c } \hline f_{CLK} > 50 \mbox{ MHz} & (10 \mbox{ mode}) > 1 \mbox{ MHz} & (-40 \mbox{ mode}) \\ \hline T_{C} & Case temperature & -40 \mbox{ mode} 85 \mbox{ mode} {\mbox{ mode} 0} \\ \hline T_{C} & Case temperature & -40 \mbox{ mode} 85 \mbox{ mode} {\mbox{ mode} 0} \\ \hline CLK + and CLK - & & & & & & & & & & & & & & & & & & $	V DDn(PP)	50MHz (all supplies)	f_{CLK} > 50MHz; f(noise) = 1Hz to 1MHz		100	IIIV		
$\begin{array}{c c c c c c c c c c c c c c c c c c c $			f _{CLK} > 50 MHz; f(noise) > 1MHz		40			
T _C Case temperature 93.1 °C CLK+ and CLK- CLK+ and CLK- V	T _A	Operating free-air temperature		-40	85	°C		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	T _C	Case temperature			93.1	°C		
$ f_{CLK\pm} \ \ \ \ \ \ \ \ \ \ \ \ \ $	CLK+ and	CLK-						
$ \begin{array}{c c} f_{CLK\pm} & Input Pixel clock frequency \\ \hline f_{CLK\pm} & Input Dixel clock frequency \\ \hline f_{CLK\pm} & Input Dixel clock frequency \\ \hline f_{CLK\pm} & Input Dixel clock frequency \\ \hline f_{CLK\pm} & CLK Input Duty Cycle \\ \hline f_{DUT-LK} & CLK Input Cycle \\ \hline f_$			1-Channel receive mode, see Figure 3	4	15			
CLX± Input Precision Requercy 3-Channel receive mode, see Figure 5 20 65 Standby mode ⁽²⁾ , See Figure 16 500 kHz Do+, D0-, D1+, D1-, D2+, D2-, CLK+, and CLK- 35 65 % D0+, D0-, D1+, D1-, D2+, D2-, CLK+, and CLK- View of differential input voltage Non-voltage Common Mode Range 70 200 mV VicM Input Voltage Common Mode Range Receive or Acquire mode 0.6 1.2 V AVICM Input Voltage Common Mode Variation between all SubLVDS inputs VicM(m) – VicM(m) with n=D0, D1, D2, or CLK -100 100 mV AVID Differential Input Voltage Amplitude Variation between all SubLVDS inputs VI _{D(n)} – V _{ICM(m)} with n=D0, D1, D2, or CLK -10 10 % AVID Differential Input Voltage Amplitude Variation between all SubLVDS VI _{D(n)} – V _{ICM(m)} and tr(n) – tr(m) with n=D0, D1, D2, or CLK -10 10 % At _{R/F} Input Rise and Fall Time RXEN at VDD; see figure 10 800 ps LSO, LS1, CPOL, SWAP, RXEN, F/S VICMOSH Itp(n) – tr(m) and tr(n) – tr(m) with n=D0, D1, D2, or CLK -100 0 0 0	f	Input Pixel clock frequency	2-Channel receive mode, see Figure 4	8	30	MHz		
$\begin{array}{ c c c c c c } \hline Standby mode^{(2)}, See Figure 16 & 500 & kHz \\ \hline Standby mode^{(2)}, See Figure 16 & 500 & kHz \\ \hline Standby mode^{(2)}, See Figure 16 & 500 & kHz \\ \hline Standby mode^{(2)}, De Figure 16 & 35 & 65 & \% \\ \hline Do+, Do-, D1+, D1-, D2+, D2-, CLK+, and CLK- & & & & & & & & & & & & & & & & & & &$	^I CLK±		3-Channel receive mode, see Figure 5	20	65			
tbuTCLK CLK Input Duty Cycle 35 65 % D0+, D0-, D1+, D1-, D2+, D2-, CLK+, and CLK- IVD-, D1+, D1-, D2+, D2-, CLK+, and CLK- Note that the the the the the the the the the th			Standby mode ⁽²⁾ , See Figure 16		500	kHz		
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	t _{DUTCLK}	CLK Input Duty Cycle		35	65	%		
	D0+, D0–,	D1+, D1–, D2+, D2-, CLK+, and CLK–				P		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	V _{ID}	Magnitude of differential input voltage	$\label{eq:started_linear} \begin{array}{l} V_{D0+} - V_{D0-} , \ V_{D1+} - V_{D1-} , \ V_{D2+} - V_{D2-} , \\ V_{CLK+} - V_{CLK-} \ during \ normal \ operation \end{array}$	70	200	mV		
Stand-by mode $0.9 \times V_{DDLVDS}$ ΔV_{ICM} Input Voltage Common Mode Variation between all SubLVDS inputs $V_{ICM(n)} - V_{ICM(m)}$ with n=D0, D1, D2, or CLK -100 100 mV ΔV_{ID} Differential Input Voltage Amplitude Variation between all SubLVDS inputs $V_{ID(n)} - V_{ID(m)}$ with n=D0, D1, D2, or CLK -10 10 ∞ ΔV_{ID} Differential Input Voltage Amplitude Variation between all SubLVDS inputs $V_{ID(n)} - V_{ID(m)}$ with n=D0, D1, D2, or CLK -10 10 ∞ ΔV_{IP} Input Rise and Fall TimeRXEN at VDD; see figure 10 800 ps $\Delta t_{R/F}$ Input Rise or Fall Time mismatch between all SubLVDS inputs $t_{R(n)} - t_{R(m)}$ and $t_{F(n)} - t_{F(m)}$ with n=D0, D1, D2, or CLK -100 100 ps LSO, LS1, CPOL, SWAP, RXEN, F/SVICMOSH W_{ID} V_{DD} V V_{ICMOSL} Low-level input voltage 0 $0.3 \times V_{DD}$ V V_{ICMOSL} Low-level input voltage 10 μ sR[7:0], G[7:0], B[7:0], VS, HS, DE, PCLK, CPE 10 μ s	VICM	Input Voltage Common Mode Range	Receive or Acquire mode	0.6	1.2	V		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			Stand-by mode	$0.9 \times V_{DDLVDS}$				
$ \begin{array}{ c c c c c } \Delta V_{ID} & \begin{tabular}{ c c c c c } Differential Input Voltage Amplitude V_{ID(n)} - V_{ID(m)} with n=D0, D1, D2, or CLK & -10 & 10 \\ and m=D0, D1, D2, or CLK & -10 & 10 \\ and m=D0, D1, D2, or CLK & -10 & 10 \\ \hline and m=D0, D1, D2, or CLK & -10 & 10 \\ \hline between all SubLVDS inputs & RXEN at VDD; see figure 10 & 800 & ps \\ \hline \Delta t_{R/F} & Input Rise or Fall Time mismatch between all SubLVDS inputs & t_{R(n)} - t_{R(m)} and t_{F(n)} - t_{F(m)} with n=D0, D1, D1, -100 & 100 \\ D2, or CLK and m=D0, D1, D2, or CLK & -100 & 0.0 \\ \hline \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	ΔV_{ICM}	Input Voltage Common Mode Variation between all SubLVDS inputs	$V_{ICM(n)}-V_{ICM(m)}$ with n=D0, D1, D2, or CLK and m=D0, D1, D2, or CLK	-100	100	mV		
$t_{R/F}$ Input Rise and Fall TimeRXEN at VDD; see figure 10800ps $\Delta t_{R/F}$ Input Rise or Fall Time mismatch between all SubLVDS inputs $t_{R(n)} - t_{R(m)}$ and $t_{F(n)} - t_{F(m)}$ with n=D0, D1, D2, or CLK and m=D0, D1, D2, or CLK-100100psLSO, LS1, CPOL, SWAP, RXEN, F/S V_{ICMOSH} High-level input voltage $0.7 \times V_{DD}$ V_{DD} V V_{ICMOSL} Low-level input voltage0 $0.3 \times V_{DD}$ V t_{inRXEN} RXEN input pulse duration10 μ sR[7:0], B[7:0], VS, HS, DE, PCLK, CPE C_L Output load capacitance10pF	ΔV_{ID}	Differential Input Voltage Amplitude Variation between all SubLVDS inputs	$V_{\text{ID}(n)}-V_{\text{ID}(m)}$ with n=D0, D1, D2, or CLK and m=D0, D1, D2, or CLK	-10	10	%		
$ \begin{array}{ c c c c c c } & & Input Rise or Fall Time mismatch \\ between all SubLVDS inputs \\ \hline \end{tabular} \between all SubLVDS input sublar \\ \hline \end{tabular} \between all SubLVDS \between all SubLVDS \between all SubLVDS \\ \hline \end{tabular} \between all SubLVDS \bet$	t _{R/F}	Input Rise and Fall Time	RXEN at VDD; see figure 10		800	ps		
LS0, LS1, CPOL, SWAP, RXEN, F/S V _{ICMOSH} High-level input voltage 0.7×V _{DD} V _{DD} V V _{ICMOSL} Low-level input voltage 0 0.3×V _{DD} V t _{inRXEN} RXEN input pulse duration 10 µs R[7:0], G[7:0], S[7:0], VS, HS, DE, PCLK, CPE 10 pF	$\Delta t_{\text{R/F}}$	Input Rise or Fall Time mismatch between all SubLVDS inputs	$t_{R(n)}-t_{R(m)}$ and $t_{F(n)}-t_{F(m)}$ with n=D0, D1, D2, or CLK and m=D0, D1, D2, or CLK	-100	100	ps		
VICMOSH High-level input voltage 0.7×V _{DD} V _{DD} V VICMOSL Low-level input voltage 0 0.3×V _{DD} V tinRXEN RXEN input pulse duration 10 µs R[7:0], G[7:0], B[7:0], VS, HS, DE, PCLK, CPE 10 pF	LS0, LS1,	CPOL, SWAP, RXEN, F/S						
VicMOSL Low-level input voltage 0 0.3×V _{DD} V t _{inRXEN} RXEN input pulse duration 10 µs R[7:0], B[7:0], VS, HS, DE, PCLK, CPE UP CL Output load capacitance 10 pF	VICMOSH	High-level input voltage		$0.7 \times V_{DD}$	V _{DD}	V		
tinRXEN RXEN input pulse duration 10 μs R[7:0], G[7:0], VS, HS, DE, PCLK, CPE 10 μs CL Output load capacitance 10 pF	VICMOSL	Low-level input voltage		0	$0.3 \times V_{DD}$	V		
R[7:0], G[7:0], VS, HS, DE, PCLK, CPE 10 pF	t _{inRXEN}	RXEN input pulse duration		10		μs		
C _L Output load capacitance 10 pF	R[7:0], G[7	R[7:0], G[7:0], B[7:0], VS, HS, DE, PCLK, CPE						
	CL	Output load capacitance			10	pF		

(1) (2)

Unused single-ended inputs must be held high or low to prevent them from floating. PCLK input frequencies lower than 500 kHz force the SN65LVDS314 into standby mode. Input frequencies between 500 kHz and 3 MHz may or may not activate the SN65LVDS314. Input frequencies beyond 3 MHz activate the SN65LVDS314. Input frequencies between 500 kHz and 4 MHz are not recommended, and can cause PLL malfunction.



DEVICE ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PA	RAMETER		TEST CONDITIO	NS		MIN TYP ⁽¹⁾	MAX ⁽²⁾	UNIT
					V _{DD_IO} = 1.8 V	7.1		
			Typical power test pattern (see Table 6);	$f_{PCLK} = 4 MHz$	V _{DD_IO} = 2.5 V	8.2		mA
			$V_{ID} = 70 \text{ mV},$ All CMOS outputs terminated with 10 pF;		V _{DD_IO} = 3.3 V	10.3		
			F/S at GND and RXEN at V_{DD} ;		V _{DD_IO} = 1.8 V	15.3		
			$V_{IH} = V_{DD}, V_{IL} = 0 V,$ $V_{DD} = V_{DDPLLA} = V_{DDPLLD} = V_{DDLVDS}$	$f_{PCLK} = 15 \text{ MHz}$	V _{DD_IO} = 2.5 V	17.4		mA
		10bM			$V_{DD_{IO}} = 3.3 V$	21		
		TCHIM			V _{DD_IO} = 1.8 V	8.9	12.3	
			Alternating 1010 Test pattern (see Table 0):	$f_{PCLK} = 4 MHz$	$V_{DD_{IO}} = 2.5 V$	10.7	12.8	mA
			All CMOS outputs terminated with 10 pF;		$V_{DD_{IO}} = 3.3 V$	13.5	16	
			F/S and RXEN at V_{DD} ; $V_{IH} = V_{DD}$, $V_{IL} = 0$ V;		$V_{DD_{IO}} = 1.8 V$	19.3	25	
			$v_{DD} = v_{DDPLLA} = v_{DDPLLD} = v_{DDLVDS}$	$f_{PCLK} = 15 \text{ MHz}$	$V_{DD_{IO}} = 2.5 V$	23.3	28.6	mA
					$V_{DD_{IO}} = 3.3 V$	28.4	35.2	
			Typical power test pattern (see Table 7); $V_{ID} = 70 \text{ mV}$, All CMOS outputs terminated with 10 pF; F/S at GND and RXEN at V_{DD} ; $V_{IH} = V_{DD}$, $V_{IL} = 0 \text{ V}$; $V_{DD} = V_{DDPLLA} = V_{DDPLLD} = V_{DDLVDS}$		$V_{DD_{IO}} = 1.8 V$	9.7		
				$f_{PCLK} = 8 MHz$	$V_{DD_{IO}} = 2.5 V$	11.3		mA
	Total Average Supply Current	2ChM			$V_{DD_{IO}} = 3.3 V$	14		
				f _{PCLK} = 30 MHz	$V_{DD_{IO}} = 1.8 V$	20.4		mA
					$V_{DD_{IO}} = 2.5 V$	24.3		
					$V_{DD_{IO}} = 3.3 V$	29.1		
DD				f _{PCLK} = 8 MHz	$V_{DD_{IO}} = 1.8 V$	12.9	17.3	mA
			Alternating 1010 Test pattern (see Table 9); All CMOS outputs terminated with 10 pF; F/S and RXEN at V_{DD} ; $V_{IH} = V_{DD}$, $V_{IL} = 0$ V; $V_{DD} = V_{DDPLLA} = V_{DDPLLD} = V_{DDLVDS}$		$V_{DD_{IO}} = 2.5 V$	15.6	19.3	
					$V_{DD_{IO}} = 3.3 V$	20.3	26.9	
				f _{PCLK} = 30 MHz	$V_{DD_{IO}} = 1.8 V$	30.4	40.4	mA
					$V_{DD_{IO}} = 2.5 V$	37.2	48.3	
					$V_{DD_{IO}} = 3.3 V$	45.9	61.7	
			Typical power test pattern (see Table 8);	f _{PCLK} = 20 MHz	V _{DD_IO} = 1.8 V	15.5		
					$V_{DD_{IO}} = 2.5 V$	19		mA
			All CMOS outputs terminated with 10 pF;		$V_{DD_{IO}} = 3.3 V$	23.5		
			F/S at GND and RXEN at V _{DD} ;		$V_{DD_{IO}} = 1.8 V$	32.9		
			$V_{\text{IH}} = V_{\text{DD}}, V_{\text{IL}} = 0 V,$ $V_{\text{DD}} = V_{\text{DDPLLA}} = V_{\text{DDPLLD}} = V_{\text{DDLVDS}}$	$f_{PCLK} = 65 \text{ MHz}$	$V_{DD_{IO}} = 2.5 V$	39.9		mA
		20.hM			$V_{DD_{IO}} = 3.3 V$	48.7		
		SCHW			$V_{DD_{IO}} = 1.8 V$	21.4	29.7	
			Alternating 1010 Test pattern (see Table 0):	$f_{PCLK} = 20 \text{ MHz}$	$V_{DD_{IO}} = 2.5 V$	26.4	33.7	mA
			All CMOS outputs terminated with 10 pF;		$V_{DD_{IO}} = 3.3 V$	33.1	41.3	
			F/S and RXEN at V_{DD} ; $V_{IH} = V_{DD}$, $V_{IL} = 0$ V;		V _{DD_IO} = 1.8 V	49.9	66.9	
			$v_{DD} = v_{DDPLLA} = v_{DDPLLD} = v_{DDLVDS}$	$f_{PCLK} = 65 \text{ MHz}$	$V_{DD_{IO}} = 2.5 V$	62.5	80.3	mA
					$V_{DD_{IO}} = 3.3 V$	77.9	102.3	
		CLK and	D[0:2] inputs are left open;	Standby mode; RX	KEN = V _{IH}	30	80	μA
		All control inputs held static high or low; All CMOS outputs terminated with 10 pF; $V_{IH} = V_{DD}$, $V_{II} = 0V$; $V_{DD} = V_{DDPLLA} = V_{DDPLLD} = V_{DDPLLD}$		Shutdown mode; RXEN = V _{IL}		0.3	6	μA

All typical values are at 25°C with V_{DD} = V_{DDPLLA} = V_{DDPLLD} = V_{DDLVDS} = 1.8 V.
 All max values are at the worst-case process corner, voltage, and temperature. The V_{DD_IO} voltage is the described voltage + 10%.

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STRUMENTS

EXAS

INPUT ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
D0+, D	0–, D1+, D1–, D2+, D2–, CLK+, and CLK–	· · · ·				
V _{thstby}	Input voltage common mode threshold to switch between receive/acquire mode and standby mode	RXEN at V _{DD}	1.3		0.9×V _{DDLVDS}	V
V_{THL}	Low-level differential input voltage threshold	V _{D0+} -V _{D0-} , V _{D1+} -V _{D1-} , V _{D2+} -V _{D2-} , V _{CLK+} -V _{CLK-}	-40			mV
V _{THH}	High-level differential input voltage threshold				40	mV
I _{I+} , I _{I-}	Input leakage current	V_{DD} =1.95 V; $V_{I+} = V_{I-}$; V _I = 0.4 V and V _I = 1.5 V			75	μA
IIOFF	Power-off input current	V_{DD} =GND; V_{I} = 1.5V			-75	μA
R _{ID}	Differential input termination resistor value		78	100	122	Ω
C _{IN}	Input capacitance	Measured between input terminal and GND		1		pF
ΔC_{IN}	Input capacitance variation	Within one signal pair			0.2	- 5
		Between all signals			1	рн
R _{BBDC}	Pull-up resistor for standby detection		21	30	39	kΩ
LS0, L	S1, CPOL, SWAP, RXEN, F/S					
V _{IK}	Input clamp voltage	I_{I} = -18 mA, V_{DD} = V_{DD} (min)			-1.2	V
I _{ICMOS}	Input current ⁽²⁾	0 V \leq V _{DD} \leq 1.95 V; V _I =GND or V _I =1.95 V			100	nA
C _{IN}	Input capacitance			2		pF
I _{IH}	High-level input current	$V_{IN} = 0.7 \times V_{DD}$	-200		200	n (
IIL	Low-level input current	$V_{IN} = 0.3 \times V_{DD}$	-200		200	TIA .
V _{IH}	High-level input voltage		$0.7 \times V_{DD}$		V _{DD}	V
VIL	Low-level input voltage		0		$0.3 \times V_{DD}$	v

(1)

All typical values are at 25°C and with 1.8 V supply unless otherwise noted. Do not leave any CMOS Input unconnected or floating to minimize leakage currents. Every input must be connected to a valid logic level (2)VIH or VOL while power is supplied to VDD.



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OUTPUT ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP I	MAX	UNIT
R[0:7	7], G[0:7], B[0:7], VS, HS, DE, PCLK, CPE		·			
Vон		1-ChM, F/S=L, I _{OH} = -250 μA				
	LP-b. Level ender door being	2-or 3-ChM, F/S=L, I _{OH} = -500 μA	0.9.1/	V		V
⊻он	High-level output voltage	1-ChM, F/S=H, Ι _{OH} = -500 μA	U.OXVDD_IO	V	DD_IO	v
		2- or 3-ChM, F/S=H, I _{OH} = -1.33 mA				
V _{OL}		1-ChM, F/S=L, I _{OL} = 250 μA		0.5		
		2- or 3-ChM, F/S=L, I _{OL} = 500 μA	0		0.5	V
	Low-level output voltage	1-ChM, F/S=H, I _{OL} = 500 μA			V _{DD_IO}	v
		2- or 3-ChM, F/S=H, I _{OL} = 1.33 mA				
		1-ChM, F/S=L	-250			
V _{OL} I _{OH}	High-level output current	2- or 3-ChM, F/S=L; 1-ChM, F/S=H	-500			
		2- or 3-ChM, F/S=H	-1333			
		1-ChM, F/S=L			250	μΑ
I _{OL}	Low-level output current	2- or 3-ChM, F/S=L; 1-ChM, F/S=H			500	
V _{OH} V _{OL} I _{OH}		2- or 3-ChM, F/S=H			1333	

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TEXAS INSTRUMENTS

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SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CO	NDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
D0+, D0-,	, D1+, D1–, D2+, D2–, CLK+, and	CLK-					
t _{R/F}	Input rise and fall time	RXEN at V _{DD} ; see figure 6-2				800	ps
∆t _{R/F}	Input rise or fall time mismatch between all SubLVDS inputs	$t_R(n)$ $t_R(m)$ and $t_F(n)$ $t_F(m)$ v and m=D0, D1, D2, or CLK	vith n=D0, D1, D2, or CLK	-100		100	ps
R[7:0], G[[7:0], B[7:0], VS, HS, DE, PCLK,	CPE					
			1-channel mode, F/S=L	8		16	
			2-channel mode, F/S=L	4		8	l
	Rise and fall time 20%-	$C_{L} = 10 \text{ pF}^{(3)}$	3-channel mode, F/S=L	4		8	-
^L R/F	80% of V_{DD_IO} $^{(2)}$	see Figure 9	1-channel mode, F/S=H	4		8	ns
			2-channel mode, F/S=H	1.3		3	I
			3-channel mode, F/S=H	1.3		3	
		1-channel and 3-channel mo	de	45%	50%	55%	
t _{OUTP}	PCLK output duty cycle	CPOL=VIL, 2-channel mode		48%	53%	59%	
		CPOL=V _{IH} , 2-channel mode		41%	47%	52%	I
t _{osk}			1-channel mode, F/S=L	-2		2	
	Output skew between PCLK and R[0:7], G[0:7], B0:7], HS, VS, and DE	see Figure 9	1-channel mode, F/S=H or 2-channel mode, F/S=L or 3-channel mode, F/S=L	-1		1	ns
			2-channel mode, F/S=H or 3-channel mode, F/S=H	-0.5		0.5	
INPUT TO	OOUTPUT RESPONSE TIME						
t _{PD(L)}	Propagation delay time from CLK+ input to PCLK output	RXEN at V_{DD} , $V_{IH}=V_{DD}$, $V_{IL}=0$ See Figure 14	GND, C _L =10 pF,	1.4/f _{PCLK}	1.9/f _{PCLK}	2.5/f _{PCLK}	S
t _{GS}	RXEN glitch to suppress pulse width ⁽⁴⁾	$V_{IH}=V_{DD}$, $V_{IL}=GND$, RXEN to See Figure 15 and Figure 16	ggles between V_{IL} and V_{IH} ;			3.8	μs
t _{pwrup}	Enable time from power down (↑RXEN)	Time from RXEN pulled high outputs valid data; See Figur	to data outputs enabled and e 16			2	ms
t _{pwrdn}	Disable time from active mode (↓RXEN)	RXEN is pulled low during re measurement until all output: R[0:7]=G[0:7]=B[0:7]=VS=HS PLL is Shutdown; See Figure	ceive mode; time s held static: S=high, DE=PCLK=low and e 16			11	μs
t _{wakeup}	Enable time from Standby (↑↓CLK)	RXEN at V _{DD} ; device is in sta from CLK input starts switchi enabled and outputting valid	andby; time measurement ng to PCLK and data outputs data; See Figure 17			2	ms
t _{standby}	Disable time from active mode (CLK transitions to high-impedance)	$\begin{array}{l} \text{RXEN at } V_{\text{DD}} \text{; device is received and } \\ \text{measurement from CLK input input common mode VICM e} \\ V_{\text{thstby}} \text{) until all outputs held s} \\ \text{R}[0:7]=\text{G}[0:7]=\text{B}[0:7]=\text{VS}=\text{HS} \\ \text{DE=PCLK=low and PLL is S} \\ \text{See Figure 17} \end{array}$	iving data; time t signal stops (input open or xceeds threshold voltage static: S=high, hutdown;			3	μs
f _{BW}	PLL bandwidth ⁽⁵⁾	Tested from CLK input to	2-ChM; f _{PCLK} =22MHz	0.087×f _{PCLK}			MHz
'BW		POLK output	3-ChM; f _{PCLK} =65MHz	0.075×f _{PCLK}			

(1) All typical values are at 25°C and with 1.8 V supply unless otherwise noted.

(2) t_{R/F} depends on the F/S setting and the capacitive load connected to each output. Some application information of how to calculate t_{R/F} based on the output load and how to estimate the timing budget to interconnect to an LCD driver are provided in the application section near the end of this data sheet.

(3) The output rise and fall time is optimized for an output load of 10 pF. This model does not take into account trace or connector loading, so the actual rise and fall times in different systems will vary.

(4) The RXEN input incorporates a glitch-suppression logic to disregard short input pulses. t_{GS} is the duration of either a high-to-low or low-to-high transition that is suppressed.

(5) When using the SN65LVDS314 receiver in conjunction with the SN65LVDS301 transmitter in one link, the PLL bandwidth of the SN65LVDS314 receiver always exceed the bandwidth of the SN65LVDS301 transmit PLL. This ensures stable PLL tracking under all operating conditions and maximizes the receiver skew margin.



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Figure 6. SN65LVDS314 PLL Bandwidth (also showing the SN65LVDS301 PLL bandwidth)

	PARAMETER	TEST CONDI	TIONS	MIN	MAX	UNIT
		1ChM: x=029, f _{PCLK} =15 MHz;	f _{CLK} =15 MHz ⁽⁴⁾	630		
t _{RSKMx} (1) (2)		RXEN at V_{DD} , $V_{IH}=V_{DD}$, $V_{IL}=GND$, $R_L=100 \Omega$, test setup as in Figure 8, test pattern as in Table 11	f _{CLK} =4 MHz to 15 MHz ⁽⁵⁾	$\frac{1}{2 \bullet 30 \bullet f_{CLK}} - 480 \text{ps}$		
		$\begin{array}{l} \text{2ChM: } x=014, \\ f_{\text{PCLK}}=30 \text{ MHz} \\ \text{RXEN at } V_{\text{DD}}, V_{\text{IH}}=V_{\text{DD}}, \\ V_{\text{IL}}=\text{GND}, R_{\text{L}}=100 \ \Omega, \text{ test setup} \\ \text{as in Figure 8, test pattern as in} \\ \text{Table 12} \end{array}$	f _{CLK} =30 MHz ⁽⁴⁾	630		
	Receiver input skew margin; see ⁽³⁾ and Figure 21		f _{CLK} =8 MHz to 30 MHz ⁽⁵⁾	$\frac{1}{2 \bullet 15 \bullet f_{CLK}} - 480\text{ps}$		ps
		3ChM:	f_{CLK} = 65 MHz ⁽⁴⁾	360		
		RXEN at V_{DD} , $V_{IH}=V_{DD}$, $V_{IL}=GND$, test setup as in Figure 8, test pattern as in Table 13	f_{CLK} = 20 MHz to 65 MHz ⁽⁵⁾	$\frac{1}{2 \bullet 10 \bullet f_{CLK}} - 410 \text{ps}$		

TIMING CHARACTERISTICS

- (1) Receiver Input Skew Margin (t_{RSKM}) is the timing margin available for transmitter output pulse position (t_{PPOS}), interconnect skew, and interconnect inter-symbol interference. tRSKM represents the reminder of the serial bit time not taken up by the receiver strobe uncertainty;. The t_{RSKM} assumes a bit error rate better than 10⁻¹².
- (2) t_{RSKM} is indirectly proportional to the internal set-up and hold time uncertainty, ISI and duty cycle distortion from the front end receiver, the skew missmatch between CLK and data D0, D1, and D2, as well as the PLL cycle-to-cycle jitter.
- (3) This includes the receiver internal set-up and hold time uncertainty, all PLL related high-frequency random and deterministic jitter components that impact the jitter budget, ISI and duty cycle distortion from the front end receiver, and the skew between CLK and data D0, D1, and D2; The pulse position min/max variation is given with a bit error rate target of 10⁻¹²; Measurements of the total jitter are taken over a sample amount of > 10⁻¹² samples.
- (4) The Minimum and Maximum Limits are based on statistical analysis of the device performance over process, voltage, and temp ranges.
- (5) These Minimum and Maximum Limits are simulated only.

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PARAMETER MEASUREMENT INFORMATION







Figure 8. Jitter Budget







Figure 9. Output Rise/Fall, Setup/Hold Time



Figure 10. SubLVDS Differential Input Rise and Fall Time Defintion



Figure 11. Equivalent Input Circuit Design

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PARAMETER MEASUREMENT INFORMATION (continued) I SWAP, CPOL, LSx, RXEN, F/S IICMOS **CMOS** Input (V _{I+}+V _I)/2 ۱_{l+} v_{icmos} RGB, VS, CLK+, Dx+ ۱<u>o</u> HS, DE, . CPE, PCLK v_{ID} Ч. CLK-, Dxv_{I+} v_{ICM} ٧o v_{I-} SubLVDS Input T **CMOS Output**

Figure 12. I/O Voltage and Current Definition



Figure 13. CMOS Output Test Circuit, Signal and Timing Definition



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PARAMETER MEASUREMENT INFORMATION (continued)







3 μs ► <20 ns **∢**−2 μs Glitch shorter than tGSwill be less than 20ns ignored Spike will be Glitch shorter rejected than tGS will be ignored RXEN tpwrup tpwrdn PCLK ICC tGS tGS RX RX disabled turns (OFF) Receiver disabled Receiver enabled Receiver aquires lock turns OFF (OFF) (ON) Figure 16. Receiver Enable/Disable Glitch Suppression Time CLK ^tstandby⁻ wakeup PCLK R[7:0], G[7:0], B[7:0], VS, HS, RX **RX** enabled RX enabled; Receiver disabled Receiver aquires lock, disabled output data valid output data (OFF) outputs still disabled invalid (OFF)

Figure 17. Standby Detection

POWER CONSUMPTION TESTS

Table 5 shows an example test pattern word.

Table	5.	Example	e Test	Pattern	Word
I GINIO	••	Example	, 1000	1 4110111	11010

Word	R[7:4], R[3:0], G[7:4], G[3:0], B[7-4], B[3-0], 0,VS,HS,DE
1	0x7C3E1E7

7 C				3				E			1				E				7								
R7	R6	R5	R4	R3	R2	R1	R0	G7	G6	G5	G4	G3	G2	G1	G0	B7	B6	B5	B4	B3	B2	B1	B0	0	VS	HS	DE
0	1	1	1	1	1	0	0	0	0	1	1	1	1	1	0	0	0	0	1	1	1	1	0	0	1	1	1

PARAMETER MEASUREMENT INFORMATION (continued)



TYPICAL IC POWER CONSUMPTION TEST PATTERN

Typical power-consumption test patterns consist of sixteen 30-bit receive words in 1-channel mode, eight 30-bit receive words in 2-channel mode and five 30-bit receive words in 3-channel mode. The pattern repeats itself throughout the entire measurement. It is assumed that every possible code on the RGB outputs has the same probability to occur during typical device operation.

Table 6. Typical IC Power Consumption Test Pattern,1-Channel Mode

Word	Test Pattern: R[7:4], R[3:0], G[7:4], G[3:0], B[7-4], B[3-0], 0,VS,HS,DE
1	0x000007
2	0xFFF0007
3	0x01FFF47
4	0xF0E07F7
5	0x7C3E1E7
6	0xE707C37
7	0xE1CE6C7
8	0xF1B9237
9	0x91BB347
10	0xD4CCC67
11	0xAD53377
12	0xACB2207
13	0xAAB2697
14	0x5556957
15	0xAAAAB3
16	0xAAAAAA5

Table 7. Typical IC Power Consumption Test Pattern,2-Channel Mode

Word	Test Pattern: R[7:4], R[3:0], G[7:4], G[3:0], B[7-4], B[3-0], 0,VS,HS,DE
1	0x000001
2	0x03F03F1
3	0xBFFBFF1
4	0x1D71D71
5	0x4C74C71
6	0xC45C451
7	0xA3aA3A5
8	0x5555553

Table 8. Typical IC Power Consumption Test Pattern,
3-Channel Mode

Word	Test Pattern: R[7:4], R[3:0], G[7:4], G[3:0], B[7-4], B[3-0], 0,VS,HS,DE
1	0xFFFFF1
2	0x000001
3	0xF0F0F01
4	0xCCCCCC1
5	0xAAAAA7

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SN65LVDS314

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MAXIMUM POWER CONSUMPTION TEST PATTERN

The maximum (or worst-case) power consumption of the SN65LVDS314 is tested using the two different test pattern shown in table. Test patterns consist of sixteen 30-bit receive words in 1-channel mode, eight 30-bit receive words in 2-channel mode, and five 30-bit receive words in 3-channel mode. The pattern repeats itself throughout the entire measurement. It is assumed that every possible code on RGB outputs has the same probability to occur during typical device operation.

Table 9. Worst-Case Power Consumption Test Pattern

Word	Test Pattern: R[7:4], R[3:0], G[7:4], G[3:0], B[7-4], B[3-0], 0,VS,HS,DE
1	0xAAAAAA5
2	0x5555555

Table 10. Worst-Case Power Consumption Test Pattern

Word	Test Pattern: R[7:4], R[3:0], G[7:4], G[3:0], B[7-4], B[3-0], 0,VS,HS,DE
1	0x000000
2	0xFFFFF7

OUTPUT SKEW PULSE POSITION and JITTER PERFORMANCE

The following test patterns are used to measure the output skew pulse position and the jitter performance of the SN65LVDS314. The jitter test pattern stresses the interconnect, particularly to test for ISI, using very long runlengths of consecutive bits, and incorporating very high and low data rates, maximizing switching noise. Each pattern is self-repeating for the duration of the test.

Word	Test Pattern: R[7:4], R[3:0], G[7:4], G[3:0], B[7-4], B[3-0], 0,VS,HS,DE
1	0x0000001
2	0x0000031
3	0x00000F1
4	0x00003F1
5	0x0000FF1
6	0x0003FF1
7	0x000FFF1
8	0x0F0F0F1
9	0x0C30C31
10	0x0842111
11	0x1C71C71
12	0x18C6311
13	0x111111
14	0x3333331
15	0x2452413
16	0x22A2A25
17	0x5555553
18	0xDB6DB65
19	0xCCCCCC1
20	0xEEEEE1
21	0xE739CE1
22	0xE38E381
23	0xF7BDEE1

Table 11. Receive Jitter Test Pattern, 1-Channel Mode



Word	Test Pattern: R[7:4], R[3:0], G[7:4], G[3:0], B[7-4], B[3-0], 0,VS,HS,DE
24	0xF3CF3C1
25	0xF0F0F01
26	0xFFF0001
27	0xFFFC001
28	0xFFFF001
29	0xFFFFC01
30	0xFFFF01
31	0xFFFFC1
32	0xFFFFF1

Table 11. Receive Jitter Test Pattern, 1-Channel Mode (continued)

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Word	Test Pattern: R[7:4], R[3:0], G[7:4], G[3:0], B[7-4], B[3-0], 0,VS,HS,DE
1	0x000001
2	0x000FFF3
3	0x8008001
4	0x0030037
5	0xE00E001
6	0x00FF001
7	0x007E001
8	0x003C001
9	0x0018001
10	0x1C7E381
11	0x3333331
12	0x555AAA5
13	0x6DBDB61
14	0x777771
15	0x555AAA3
16	0xAAAAA5
17	0x555553
18	0xAAA5555
19	0x8888881
20	0x9242491
21	0xAAA5571
22	0xCCCCCC1
23	0xE3E1C71
24	0xFFE7FF1
25	0xFFC3FF1
26	0xFF81FF1
27	0xFE00FF1
28	0x1FF1FF1
29	0xFFCFFC3
30	0x7FF7FF1
31	0xFFF0007
32	0xFFFFF1

Table 12. Receive Jitter Test Pattern, 2-Channel Mode



Word	Test Pattern: R[7:4], R[3:0], G[7:4], G[3:0], B[7-4], B[3-0], 0,VS,HS,DE
1	0x000001
2	0x000001
3	0x000003
4	0x0101013
5	0x0303033
6	0x0707073
7	0x1818183
8	0xE7E7E71
9	0x3535351
10	0x0202021
11	0x5454543
12	0xA5A5A51
13	0xADADAD1
14	0x5555551
15	0xA6A2AA3
16	0xA6A2AA5
17	0x555553
18	0x5555555
19	0xAAAAAA1
20	0x5252521
21	0x5A5A5A1
22	0xABABAB1
23	0xFDFCFD1
24	0xCAAACA1
25	0x1818181
26	0xE7E7E71
27	0xF8F8F81
28	0xFCFCFC1
29	0xFEFEFE1
30	0xFFFFF
31	0xFFFFF5
32	0xFFFFF5

Table 13. Receive Jitter Test Pattern, 3-Channel Mode



TYPICAL CHARACTERISTIC CURVES

The SN65LVDS314 device has very similar parametric curves as the SN65LVDS302. Please refer to this section in the SN65LVDS302 datasheet (SLLS733) for a general understanding of SN65LVDS314 characteristics.



APPLICATION INFORMATION

Preventing Increased Leakage Currents in Control Inputs

A floating (left open) CMOS input allows leakage currents to flow from V_{DD} to GND. Do not leave any CMOS input unconnected or floating. Every input must be connected to a valid logic level V_{IH} or V_{OL} while power is supplied to V_{DD} . This also minimizes the power consumption of standby and power down mode.

Power Supply Design Recommendation

For a multilayer PCB, it is recommended to keep one common GND layer underneath the device and connect all ground terminals directly to this plane.

SN65LVDS314 DECOUPLING RECOMMENDATION

The SN65LVDS314 was designed to operate reliably in a constricted environment with other digital switching ICs. In many designs, the SN65LVDS314 often shares a power supply with various other ICs. The SN65LVDS314 can operate with power supply noise as specified in Recommend Device Operating Conditions. To minimize the power supply noise floor, provide good decoupling near the SN65LVDS314 power pins. The use of four ceramic capacitors (two 0.01 μ F and two 0.1 μ F) provides good performance. At the very least, it is recommended to install one 0.1 μ F and one 0.01 μ F capacitor near the SN65LVDS314. To avoid large current loops and trace inductance, the trace length between decoupling capacitor and IC power inputs pins must be minimized. Placing the capacitor underneath the SN65LVDS314 on the bottom of the PCB is often a good choice.

VGA APPLICATION

Figure 18 shows a possible implementation of a standard 640x480 VGA display. The LVDS301 interfaces to the SN65LVDS314, which is the corresponding receiver device to deserialize the data and drive the display driver. The pixel clock rate of 22 MHz assumes ~10% blanking overhead and 60 Hz display refresh rate. The application assumes 24-bit color resolution. Also shown is how the application processor provides a powerdown (reset) signal for both serializer and the display driver. The signal count over the Flexible Printed Circuit board (FPC) could be further decreased by using the standby option on the SN65LVDS314 and pulling RXEN high with a 30 k Ω resistor to V_{DD}.





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DUAL LCD-DISPLAY APPLICATION

The example in Figure 19 shows a possible application setup driving two video-mode displays from one application processor. The data rate of 330 Mbps at a pixel clock rate of 5.5 MHz corresponds to a 320x240 QVGA resolution at 60 Hz refresh rate and 10% blanking overhead.



Figure 19. Example Dual-QVGA Display Application

TYPICAL APPLICATION FREQUENCIES

The SN65LVDS314 supports pixel clock frequencies from 4 MHz to 65 MHz over 1, 2, or 3 data lanes. Table 14 provides a few typical display resolution examples and shows the number of data lanes necessary to connect the SN65LVDS314 with the display. The blanking overhead is assumed to be 20%. Often, blanking overhead is smaller, resulting in a lower data rate. Furthermore, the examples in the table assumes a display frame refresh rate of 60-Hz. The actual refresh rate may differ depending on the application-processor clock implementation.

Display Screen	Visible	Blanking Display		Pixel Clock Frequency	Serial Data Rate Per Lane				
Resolution	Pixel Count	Overhead	Refresh Rate	[MHz]	1-ChM	2-ChM	3-ChM		
176x220 (QCIF+)	38,720	20%	90 Hz	4.2 MHz	125 Mbps				
240x320 (QVGA)	76,800	20%	60 Hz	5.5 MHz	166 Mbps				
640x200	128,000	20%	60 Hz	9.2 MHz	276 Mbps	138 Mbps			
352x416 (CIF+)	146,432	20%	60 Hz	10.5 MHz	316 Mbps	158 Mbps			
352x440	154,880	20%	60 Hz	11.2 MHz	335 Mbps	167 Mbps			
320x480 (HVGA)	153,600	20%	60 Hz	11.1 MHz	332 Mbps	166 Mbps			
800x250	200,000	20%	60 Hz	14.4 MHz	432 Mbps	216 Mbps			
640x320	204,800	20%	60 Hz	14.7 MHz	442 Mbps	221 Mbps			
640x480 (VGA)	307,200	20%	60 Hz	22.1 MHz		332 Mbps	221 Mbps		
1024x320	327,680	20%	60 Hz	23.6 MHz		354 Mbps	236 Mbps		
854x480 (WVGA)	409,920	20%	60 Hz	29.5 MHz		443 Mbps	295 Mbps		
800x600 (SVGA)	480,000	20%	60 Hz	34.6 MHz			346 Mbps		
1024x768 (XGA)	786,432	20%	60 Hz	56.6 MHz			566 Mbps		

Table 14. Typical Application Data Rates and Serial Lane Usage



CALCULATION EXAMPLE: HVGA DISPLAY

The following calculation shows an example for a Half-VGA display with the following parameters:

Display Resolution:	480 x 320 58 4 Hz	H	sync =5	Q Usible area = 480 Columns HFP=20
Horizontal Visible Pixel:	480 columns	Vsync =5		
Horizontal Front Porch:	20 columns	VBP=3		
Horizontal Sync:	5 columns			
Horizontal Back Porch:	3 columns	Visible area =320 lines		Visible area
Vertical Visible Pixel:	320 lines			
Vertical Front Porch:	10 lines		,	
Vertical Sync:	5 lines			
Vertical Back Porch:	3 lines	VFP=10	<u>. </u>	Entire Display

Figure 20. HVGA Display

Calculation of the total number of pixel and blanking overhead:Visible Area Pixel Count: $480 \times 320 = 153600$ pixelTotal Frame Pixel Count: $(480+20+5+3) \times (320+10+5+3) = 171704$ pixelBlanking Overhead: $(171704-153600) \div 153600 = 11.8 \%$

The application requires the following serial-link parameters:

Pixel Clk Frequency:	171704 × 58.4 Hz = 10.0 MHz
Serial Data Rate:	1-channel mode: 10.0 MHz × 30 bit/channel = 300 Mbps
	2-channel mode: 10.0 MHz × 15 bit/channel = 150 Mbps

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How To Determine Interconnect Skew and Jitter Budget

Designing a reliable data link requires examining the interconnect skew and jitter budget. The sum of all transmitter, PCB, connector, FPC, and receiver uncertainties must be smaller than the available serial bit time. The highest pixel clock frequency defines the available serial bit time. The transmitter timing uncertainty is defined by t_{PPOS} in the transmitter data sheet. For a bit-error-rate target of \leq 10-12, the measurement duration for tPPOS is \geq 1012. The SN65LVDS314 receiver can tolerate a maximum timing uncertainty defined by t_{RSKM} . The interconnect budget is calculated by:

 $t_{int\,erconnect} = t_{RSKM} - t_{PPOS}$

Example:

f_{PCLK}(max) = 23 MHz (VGA display resolution, 60 Hz)

Transmission mode: 2-ChM; t_{PPOS}(SN65LVDS301) = 330 ps

Target bit error rate: 10⁻¹²

 $t_{RSKM}(SN65LVDS314) = 1/(2*15*f_{PCLK}) - 480 \text{ ps} = 969 \text{ ps}$

The interconnect budget for cable skew and ISI needs to be smaller than:

 $t_{int\,erconnect} = t_{RSKM} - t_{PPOS} = 639 ps$



Figure 21. Jitter Budget

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(1)



F/S-PIN SETTING AND CONNECTING THE SN65LVDS314 TO AN LCD DRIVER

NOTE

Receiver PLL tracking: To maximize the design margin for the interconnect, good RX PLL tracking of the TX PLL is important. FlatLink3G requires the RX PLL to have a bandwidth higher than the bandwidth of the TX PLL. The SN65LVDS314 PLL design is optimized to track the SN65LVDS0301 PLL particularly well, thus providing a very large receiver skew margin. A FlatLink3G-compliant link must provide at least ±225 ppm of receiver skew margin for the interconnect.

It is important to understand the tradeoff between power consumption, EMI, and maximum speed when selecting the F/S signal. It is beneficial to choose the slowest rise time possible to minimize EMI and power consumption. Unfortunately a slower rise time also reduces the timing margin left for the LCD driver. Hence it is necessary to calculate the timing margin to select the correct F/S pin setting.

The output rise time depends on the output driver strength and the output load. An LCD driver typical capacitive load is assumed with ~10pF. The higher the capacitive load, the slower will be the rise time. Rise time of the SN65LVDS314 is measured as the time duration it takes the output voltage to rise from 20% of V_{DD} and 80% of V_{DD} and fall time is defined as the time for the output voltage to transition from 80% of V_{DD} down to 20%.

Within one mode of operation and one F/S pin setting, the rise time of the output stage is fixed and does not adjust to the pixel frequency. Due to the short bit time at very fast pixel clock speeds and the real capacitive load of the display driver, the output amplitude might not reach V_{DD} and GND saturation fully. To ensure sufficient signal swing and verify the design margin, it becomes necessary to determine that the output amplitude under any circumstance reaches the display driver's input stage logic threshold (usually 30% and 70% of V_{DD}).

Figure 22 shows a worst-case rise time simulation assuming a LCD driver load of 16pF at VGA display resolution and a $V_{DD_{IO}}$ of 1.8 V. PCLK is the fastest switching output. With F/S set to GND (Figure 22-a), the PCLK output voltage amplitude is significantly reduced. The voltage amplitude of the output data RGB[7:0], VS, HS, and DE shows less amplitude attenuation because these outputs carry random data pattern and toggle equal or less than half of the PCLK frequency. It is necessary to determine the timing margin between the LVDS314 output and LCD driver input.



Figure 22. Output Amplitude as a Function of Output Toggling Frequency, Capacitive Load and F/S Setting

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time of the LCD driver, and specify the output load of the SN65LVDS314 as a combination of the LCD driver input parasitics plus any capacitance caused by the connecting PCB trace. Furthermore, the setting of pin F/S and the SN65LVDS314 output skew impact the margin. The total remaining design margin calculates as following:

To determine the timing margin, it is necessary to specify the frequency of operation, identify the set-up and hold

$$t_{DM} = \frac{1}{2 \times f_{PCLK}} - t_{DUTP(max_error)} - \frac{t_{rise(max)} \times C_{LOAD}}{10 \text{ pF}} - |t_{OSK}|$$

HOW TO DETERMINE THE LCD DRIVER TIMING MARGIN

where:

t_{DM} – Design margin f_{PCLK} – Pixel clock frequency t_{DUTP(max error)} – maximum duty cycle error trise(max) - maximum rise or fall time; see t_{R/F} under switching characteristics C_1 – parasitic capacitance (sum of LCD driver input parasitics + connecting PCB trace) tskew - clock to data output skew SN65LVDS314

Example:

At a pixel clock frequeny of 5.5MHz (QVGA), and an assumed LCD driver load of 15 pF, the remaining timing margin is:

 $t_{DUTP(max_error)} = \frac{|t_{DUTP}(max) - 50|}{100\%} \times t_{PCLK} = \frac{5\%}{100\%} \times \frac{1}{5.5MHz} = 9.1ns$ $t_{DM} = \frac{1}{2 \times 5.5 MHz} - 9ns - \frac{16ns_{(F/S=GND)} \times 15pF}{10pF} - 500ps = 57.3ns$

As long as the set-up and hold time of the LCD driver are each less than 57 ns, the timing budget is met sufficiently.





6-Feb-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
SN65LVDS314RSKR	ACTIVE	VQFN	RSK	64	2000	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 85	LVDS314	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



1	*All dimensions are nominal												
	Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
	SN65LVDS314RSKR	VQFN	RSK	64	2000	330.0	16.4	8.3	8.3	1.1	12.0	16.0	Q2

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

5-Jun-2017



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LVDS314RSKR	VQFN	RSK	64	2000	367.0	367.0	38.0



NOTES: All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5-1994. A.

- This drawing is subject to change without notice. Β.
- C.
- QFN (Quad Flatpack No-Lead) Package configuration. The package thermal pad must be soldered to the board for thermal and mechanical performance. D.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.



RSK (S-PVQFN-N64)

PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



NOTE: A. All linear dimensions are in millimeters





NOTES:

A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SCBA017, SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.

D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.

E. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for any larger diameter vias placed in the thermal pad.



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